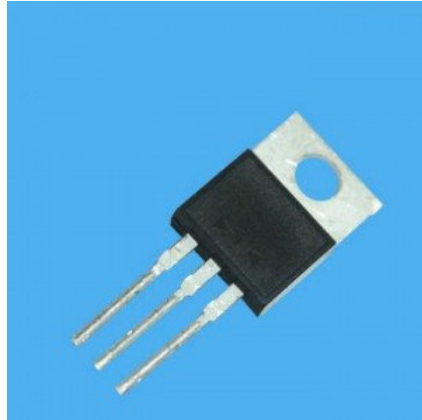




Bipolar Transistor 13005



13005 TRANSISTOR (NPN)

FEATURES

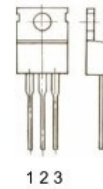
* power switching applications

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	700	V
V _{CE0}	Collector-Emitter Voltage	400	V
V _{EB0}	Emitter-Base Voltage	9	V
I _C	Collector Current -Continuous	4	A
P _C	Collector Power Dissipation	2	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-220

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CB0}	I _C = 1mA, I _E =0	700			V
Collector-emitter breakdown	V _{(BR)CE0}	I _C = 10mA, I _B =0	400			V
Emitter-base breakdown voltage	V _{(BR)EB0}	I _E = 1mA, I _C =0	9			V
Collector cut-off current	I _{CB0}	V _{CB} = 700V, I _E =0			1	mA
Collector cut-off current	I _{CE0}	V _{CE} = 400V, I _B =0			0.1	mA
Emitter cut-off current	I _{EB0}	V _{EB} =7V, I _C =0			0.05	mA
DC current gain	h _{FE1}	V _{CE} = 5V, I _C = 1A	10		60	
	h _{FE2}	V _{CE} = 5V, I _C = 10mA	5			
	h _{FE3}	V _{CE} = 5V, I _C = 2A	8		40	
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =1A, I _B =0.2A			0.3	V
	V _{CE(sat)2}	I _C =4A, I _B =1A			0.8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =2A, I _B =0.5A			1.6	V
Transition Frequency	f _T	V _{CE} =10V, I _C =500mA, f = 1MHz	5			MHz
Fall time	t _f	I _{B1} =-I _{B2} =0.4A, I _C =2A, V _{CC} =120V			0.6	μs
Storage time	t _s	I _C =0.25A	1.8		6.6	μs